



HSD879D

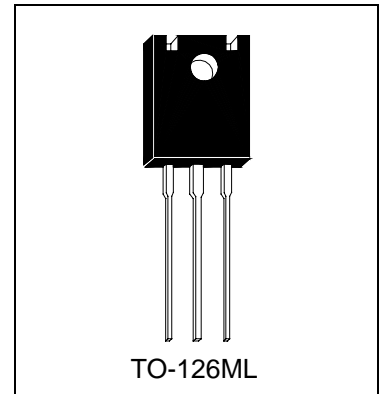
SILICON NPN EPITAXIAL TYPE TRANSISTOR

Description

For 1.5V and 3v electronic flash use.

Features

- Charger-up time is about 1 ms faster than of a germanium transistor.
- Small saturation voltage can bring less power dissipation and flashing times.



Absolute Maximum Ratings

- Maximum Temperatures
 Storage Temperature -55 ~ +150 °C
 Junction Temperature +150 °C Maximum
- Maximum Power Dissipation
 Total Power Dissipation (Ta=25°C) 1.4 W
- Maximum Voltages and Currents (Ta=25°C)
 BVCBO Collector to Base Voltage 30 V
 BVCEX Collector to Emitter Voltage 20 V
 BVCEO Collector to Emitter Voltage 10 V
 BVEBO Emitter to Base Voltage 6 V
 IC Collector Current 3 A
 IC Collector Current (Pluse) 5 A

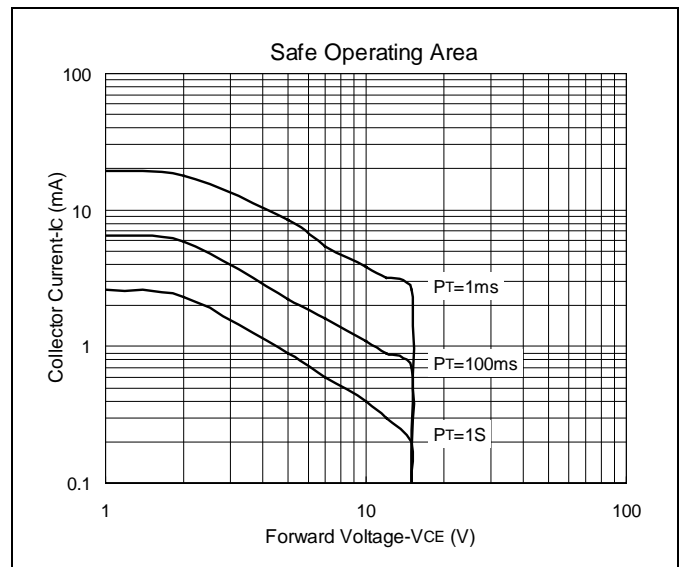
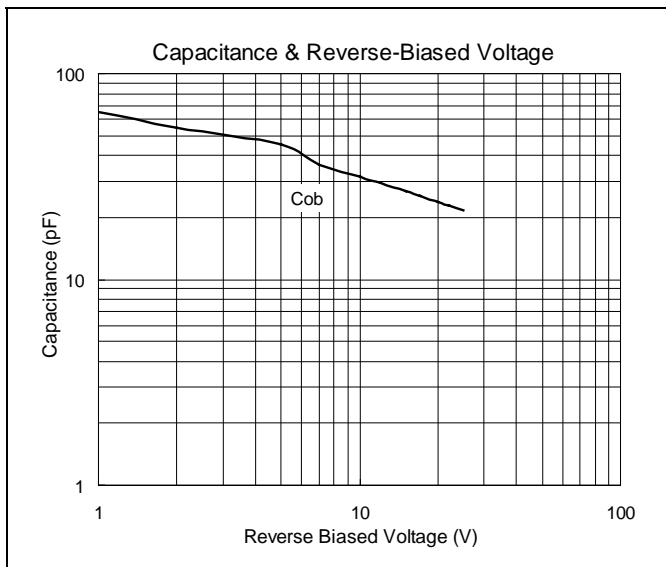
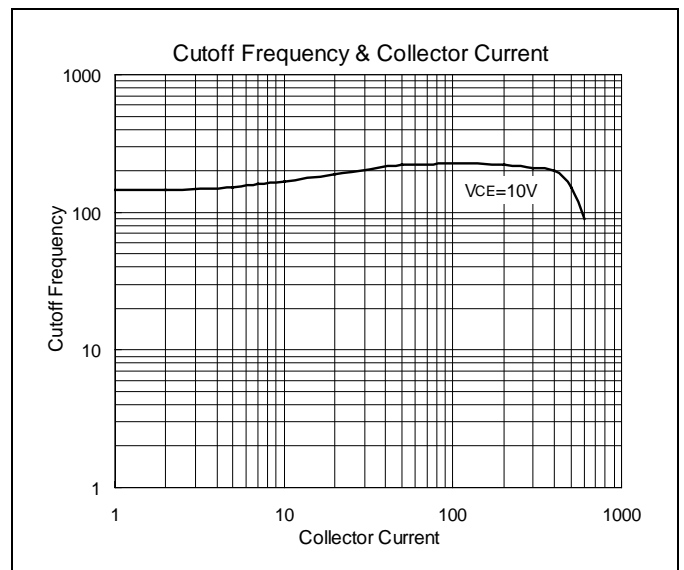
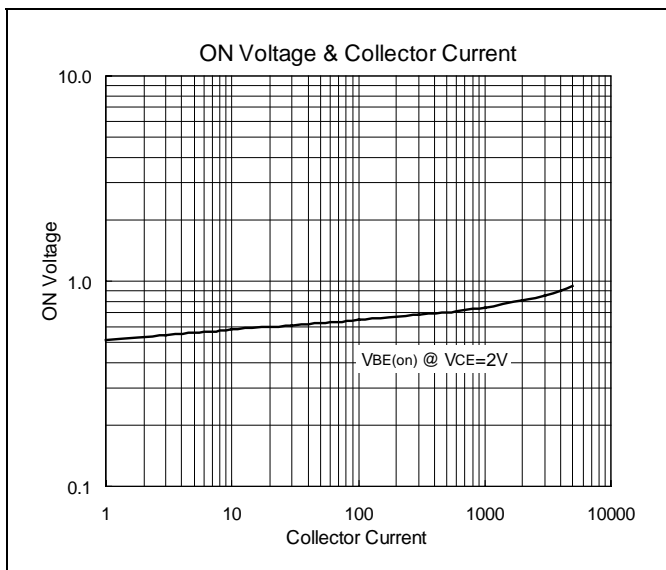
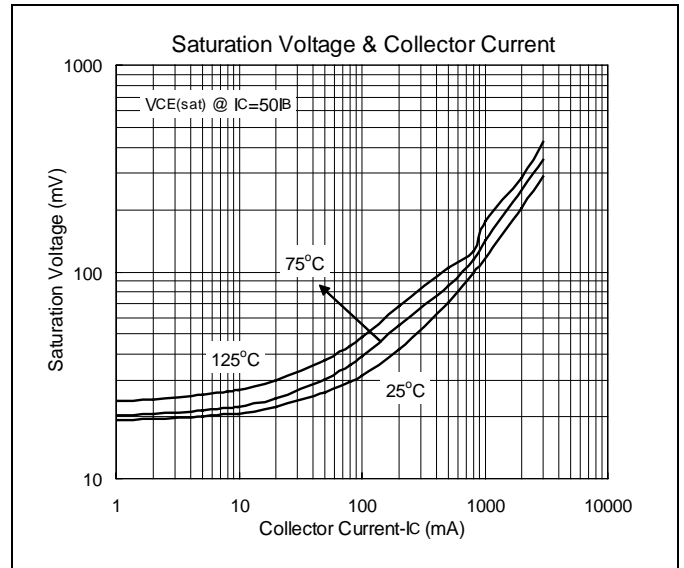
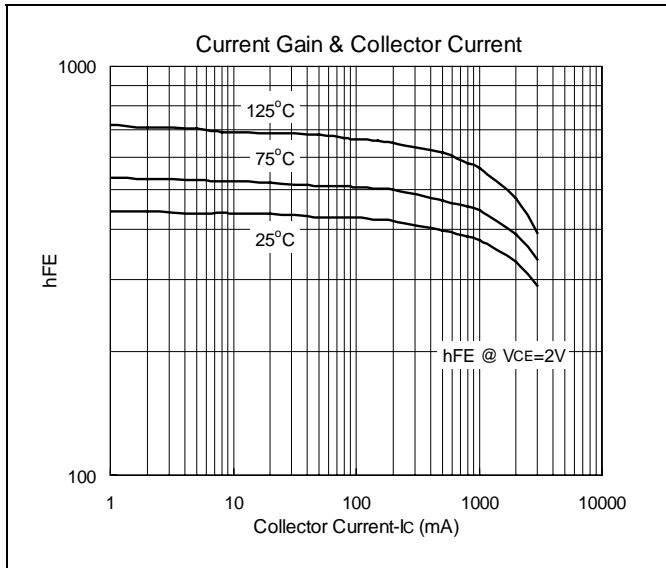
Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Condition
BVCEO	10	-	-	V	IC=1mA
BVEBO	6	-	-	V	IE=10uA
ICBO	-	-	100	nA	VCB=20V
IEBO	-	-	100	nA	VBE=4V
*VCE(sat)	-	0.3	0.4	V	IC=3A, IB=60mA
*VBE	-	0.83	1.5	V	VCE=-1V, IC=-2A
*hFE	140	210	-		VCE=2V, IC=3A
fT	-	200	-	MHZ	VCE=10V, IC=50mA
Cob	-	30	-	pF	VCB=10V, f=1KHZ

*Pulse Test: Pulse Width ≤380us, Duty Cycle≤2%

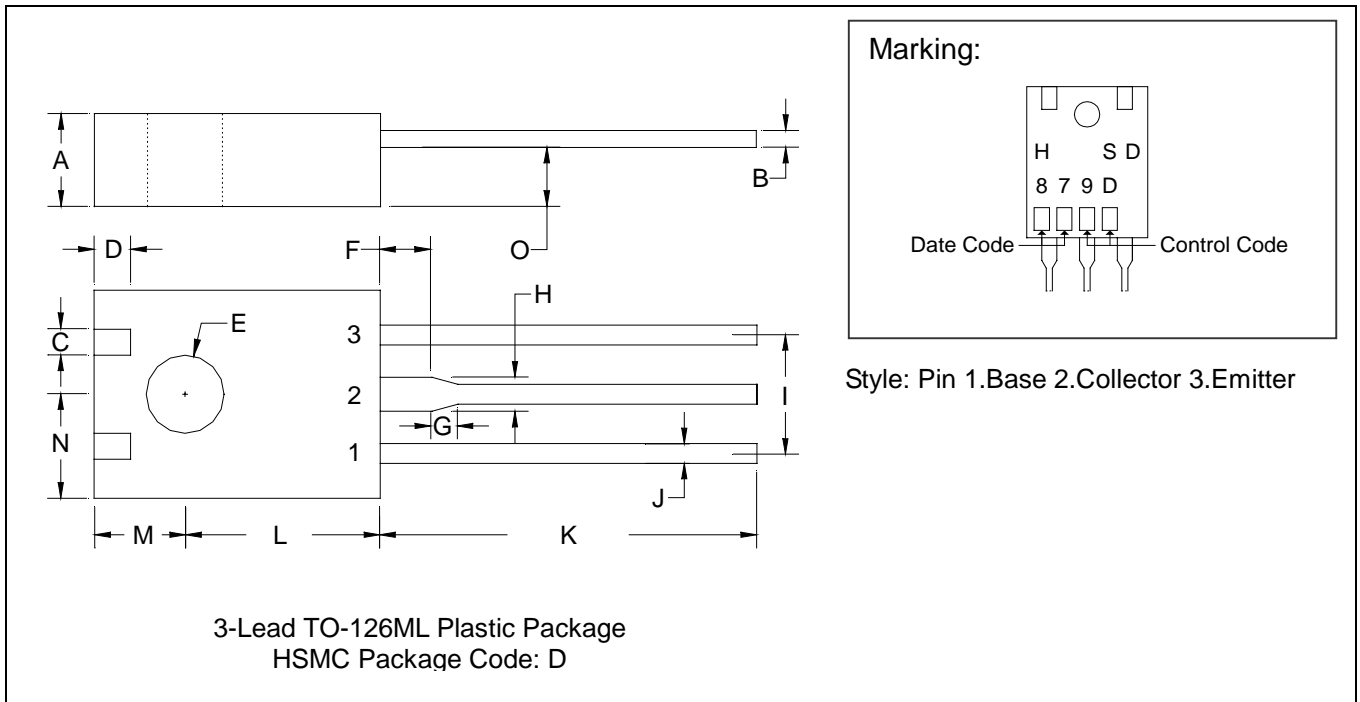


Characteristics Curve





TO-126ML Dimension



*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1356	0.1457	3.44	3.70	I	-	*0.1795	-	*4.56
B	0.0170	0.0272	0.43	0.69	J	0.0268	0.0331	0.68	0.84
C	0.0344	0.0444	0.87	1.12	K	0.5512	0.5906	14.00	15.00
D	0.0501	0.0601	1.27	1.52	L	0.2903	0.3003	7.37	7.62
E	0.1131	0.1231	2.87	3.12	M	0.1378	0.1478	3.50	3.75
F	0.0737	0.0837	1.87	2.12	N	0.1525	0.1625	3.87	4.12
G	0.0294	0.0494	0.74	1.25	O	0.0740	0.0842	1.88	2.14
H	0.0462	0.0562	1.17	1.42					

Notes: 1.Dimension and tolerance based on our Spec. dated Mar. 6,1995.
 2.Controlling dimension: millimeters.
 3.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 4.If there is any question with packing specification or packing method, please contact your local HSMC sales office.

Material:

- Lead: 42 Alloy; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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